

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	411	TFT and (polycrystal\$8 near9 island) and ((substrate or semiconductor or wafer) near9 island)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 09:49
L2	133	TFT and (polycrystal\$8 near9 island) and ((substrate or semiconductor or wafer) near9 island) and (crystal near4 grain)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 09:50
L3	1	TFT and (polycrystal\$8 near9 island) and ((substrate or semiconductor or wafer) near9 island) and (crystal near4 grain) and (strip near9 island)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 09:51
L4	1	(TFT or transistor) and (polycrystal\$8 near9 island) and ((substrate or semiconductor or wafer) near9 island) and (crystal near4 grain) and (strip near9 island)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 09:52
L5	6222	(TFT or transistor) and (semiconductor near4 island)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 09:52
L6	6222	(TFT or transistor) and (semiconductor near4 island) and (island near9 (semiconductor or substrate or wafer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 09:53
L7	2447	(TFT or transistor) and (semiconductor near4 island) and (island near9 (substrate or wafer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 09:53

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L8	54	(TFT or transistor) and (semiconductor near4 island) and (island near9 (substrate or wafer)) and (strip near9 island)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 09:53
L9	42	(TFT or transistor) and (semiconductor near4 island) and (island near9 (substrate or wafer)) and (strip near9 island) and ((insulat\$4 or oxide or dielectric) near9 island)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 09:55
L10	19	(TFT or transistor) and (semiconductor near4 island) and (island near9 (substrate or wafer)) and (strip near9 island) and ((insulat\$4 or oxide or dielectric) near9 island) and (strip near9 gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 09:55
L11	16	(TFT or transistor) and (semiconductor near4 island) and (island near9 (substrate or wafer)) and (strip near9 island) and ((insulat\$4 or oxide or dielectric) near9 island) and (strip near9 gate) and (source near9 gate) and (drain near9 gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 10:07
L12	2	(TFT or transistor) and (semiconductor near4 island) and (island near9 (substrate or wafer)) and (strip near9 island) and ((insulat\$4 or oxide or dielectric) near9 island) and (strip near9 gate) and (source near9 gate) and (drain near9 gate) and (crystal near9 grain)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 10:12
L13	5	(TFT or transistor) and (semiconductor near4 island) and (island near9 (substrate or wafer)) and (strip near9 island) and (crystal near9 grain)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 10:14
L14	3394	(TFT or transistor) and (strip near9 gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 10:14

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L15	67	(TFT or transistor) and (strip near9 gate) and (crystal near9 grain)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 10:14
L16	18	(TFT or transistor) and (strip near9 gate) and (crystal near9 grain) and (semiconductor near9 island)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 10:15
L17	14	(TFT or transistor) and (strip near9 gate) and (crystal near9 grain) and ((semiconductor near9 island) near9 (substrate or wafer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 10:15
L18	14	(TFT or transistor) and (strip near9 gate) and (crystal near9 grain) and ((semiconductor near9 island) near9 (substrate or wafer)) and ((insulat\$4 or oxide or dielectric) near9 island)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 10:17
L19	14	(TFT or transistor) and (strip near9 gate) and (crystal near9 grain) and ((semiconductor near9 island) near9 (substrate or wafer)) and (((insulat\$4 or oxide or dielectric) near9 island) and strip near9 gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 10:18
L20	9	(TFT or transistor) and (strip near9 gate) and (crystal near9 grain) and ((semiconductor near9 island) near9 (substrate or wafer)) and (((insulat\$4 or oxide or dielectric) near9 island) and strip near9 gate) and (source near9 island) and (drain near9 island)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 10:19
L21	9	(TFT or transistor) and (strip near9 gate) and (crystal near9 grain) and ((semiconductor near9 island) near9 (substrate or wafer)) and ((insulat\$4 or oxide or dielectric) near9 island) and (source near9 island) and (drain near9 island)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 10:19

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L22	14	(TFT or transistor) and (strip near9 gate) and (crystal near9 grain) and ((semiconductor near9 island) near9 (substrate or wafer))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 10:20
L23	600	(TFT and transistor) and (polycrystal\$4 near9 island)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 10:21
L24	560	(TFT and transistor) and (polycrystal\$4 near9 island) and (crystal near9 grain)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 10:26
L25	230	(TFT and transistor) and (polycrystal\$4 near9 island) and (crystal near9 grain)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 10:27
L26	4	(TFT and transistor) and (polycrystal\$4 near9 island) and (crystal near9 grain) and (strip near9 gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 10:37
L27	214	(TFT and transistor) and (polycrystal\$4 near9 island) and (crystal near grain)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 10:37
L28	27	(TFT and transistor) and (polycrystal\$4 near9 island) near9 (substrate or wafer) and (crystal near grain)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 10:44

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L29	1	(TFT and transistor) and (polycrystal\$4 near9 island) near9 (substrate or wafer) and (crystal near grain) and (strip near9 (island or region))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 10:38
L30	1	(TFT and transistor) and (polycrystal\$4 near9 island) near9 (substrate or wafer) and (crystal near grain) and (strip near9 (island or region or gate))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 10:39
L31	2928	(semiconductor near island)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 10:44
L32	34	(semiconductor near island) and saw	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 10:44
L33	10	(semiconductor near island) and (saw near9 edge)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 10:46
L34	1	(semiconductor near island) and (strip near9 peninsula)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 11:13
L35	2089	ratio near9 (crystal near grain)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 11:13

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L36	256	ratio near9 (crystal near grain) and (TFT or transistor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 11:13
L37	1	ratio near9 (crystal near grain) and (TFT or transistor) and (strip near gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 11:14
L38	1	ratio near9 (crystal near grain) and (TFT or transistor) and (strip near9 gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 11:14
L39	225	ratio near9 (crystal near grain) and (TFT or transistor) and gate	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 11:14
L40	15	ratio near9 (crystal near grain) and (TFT or transistor) and gate and source and drain and strip	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 11:15
S1	0	TFT and (polycrystal\$8 near9 island) and ((substrate or semiconductor or wafer) near9 island)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 08:34
S2	411	TFT and (polycrystal\$8 near9 island) and ((substrate or semiconductor or wafer) near9 island)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 08:34

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S3	213	TFT and (polycrystal\$8 near9 island) and ((substrate or semiconductor or wafer) near9 island) and ((insulat\$4 or oxide or dielectric) near9 island)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 08:35
S4	0	TFT and (polycrystal\$8 near9 island) and ((substrate or semiconductor or wafer) near9 island) and ((insulat\$4 or oxide or dielectric) near9 island) and (strip near gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 08:35
S5	6	TFT and (polycrystal\$8 near9 island) and ((substrate or semiconductor or wafer) near9 island) and ((insulat\$4 or oxide or dielectric) near9 island) and (strip near9 gate)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 08:36
S6	6	TFT and (polycrystal\$8 near9 island) and ((substrate or semiconductor or wafer) near9 island) and ((insulat\$4 or oxide or dielectric) near9 island) and (strip near9 gate) and (source near9 island)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 08:36
S7	3	TFT and (polycrystal\$8 near9 island) and ((substrate or semiconductor or wafer) near9 island) and ((insulat\$4 or oxide or dielectric) near9 island) and (strip near9 gate) and (source near9 island) and (drain near9 island)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/01/18 09:49